REMARKS

In response to the Examiner's Action mailed on June 28, 2004, the Specification is amended, claims 1, 6, 7, 11, 16, and 17 are canceled and claims 2-5, 8-10, 12-15, and 18-20 are amended. The applicant hereby respectfully requests that the patent application be reconsidered.

An item-by-item response to Examiner's objections or rejections is provided in the followings:

1. ***Objection to Specification and Claims***

The Examiner objects to the disclosure because of the following informalities: on page 2, line 5, *"IA"* and "1B" should read "1(a)" and "1(b)", respectively. On page 5, line 2, "358" should be "318". Claims 6 and 16 are objected to because of the following informalities: "ploy" should be changed to "poly".

In response to the objections, the Specification and claims 6 and 16 are amended and the informalities are corrected.

2. ***Claim Rejections - 35 USC102***

The Examiner rejects Claims 1, 3, 5-7, 10, 11, 13, 15-17 and 20 under 35 U.S.C. 102(b) as being anticipated by Tsunoda. According to the Examiner, as to claim 1, Tsunoda, Figure 1, discloses an electronic device supported on a semiconductor substrate comprising a diffusion area *(105)* (col. 3, line 46) in said substrate and a polysilicon area (109) (col. 3, lines 57-58) comprising a polysilicon layer extending over said substrate for contacting said diffusion area, and a single contact (110) (col. 3, line 60) disposed on top of said substrate contacting both said polysilicon layer and said diffusion layer. As to claim 3, since the contact layer (110) is itself

metal, it is within the scope of a metal layer disposed on top of said single contact. As to claim 5, Tsunoda, Figure 9, discloses an embodiment where the diffusion area comprises a source/drain of a transistor (col. 9, line 11). As to claim 6, Tsunoda, Figure 1, discloses a poly-to-diffusion connection disposed on a substrate comprising a diffusion area (105) in said substrate and a polysilicon area (109) comprising a polysilicon layer extending over said substrate for contacting said diffusion area. As to claim 7, Tsunoda, Figure 1, discloses a single contact (110) disposed on top of said substrate contacting both said polysilicon layer and said diffusion area. As to claim 10, since the contact layer (110) is itself metal, it is within the scope of a metal layer disposed on top of said single contact. As to claims 11, 13, 15-17 and 20, the device of Tsunoda would necessarily have to be formed in order to function, so that the method comprising the formation of the device is inherent in the device structure itself.

In response to the rejections, claims 1, 6, 7, 11, 16, and 17 are canceled and claim 2-5, 8-10, 12-15, and 18-20 are amended.

According to the allowability of the claims as set forth below the amended claims would be allowable.

3. Allowable Subject Matter

The Examiner instructs that Claims 2, 4, 8, 9,12, 14,18 and 19 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims. Tsunoda is the best prior art, but does not disclose the polysilicon layer formed on top of a field oxide formed next to the diffusion area. Tsunoda also does not disclose the single contact filling an opening etched in an insulating layer formed over the diffusion area.

In response to the instructions, claims 2-5, 8-10, 12-15, and 18-20 are amended and the allowable but objected claim are rewritten as independent claims to include all the elements of the base and all the intervening claims. All the dependent claims are now depend on allowable claims.

With the canceled and the amended claims and the reasons provided above, the Applicant respectfully requests that the rejections be withdrawn and the Patent Application as amended now be allowed.

Respectfully submitted
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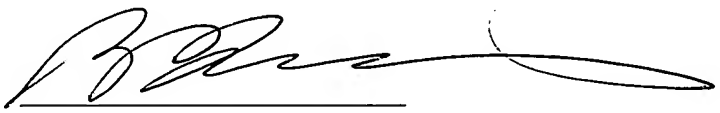
By 

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